			Docket Number (Optional)  FIS920030230US1  Application N		Application Number	lumber			
PIAFORMATION DISCLOSURE CITATION  (Use several sheets if necessary)  OCT 0 6 2003 5				Applicant(s) Bruley et al					
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OCT US DATE			2814						
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B		Gate Dielectric," Roton	daro et al., pp. 1	48-149.	chnical Papers, "Advanc				
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INFO		ATION DISCLOSURE CITATION (Use several sheets if necessary)	Applicant(s) Bruley et al			
			Filing Date	Group Art Unit 2814		
•EXAMINER IMITAL		OTHER DOCUMENTS (Including Author, 1	Title, Date, Pertinent Pages, Etc.)			
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		citation considered, whether or not citation is in conform copy of this form with next communication to applicant.		ne through citation if not in conformance and		

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## **ELECTRONIC INFORMATION DISCLOSURE STATEMENT**

## Electronic Version v18

Stylesheet Version v18.0

Title of Invention

CAPACITOR AND FABRICATION METHOD USING ULTRA-HIGH VACUUM CVD OF SILICON NITRIDE

Application Number:

Confirmation Number:

First Named Applicant:

John Bruley

Attorney Docket Number: FIS920030230US1

Art Unit:

Examiner:

Search string:

(5943560 or 5540785 or 5462883).pn

## **US Patent Documents**

Note: Applicant is not required to submit a paper copy of cited US Patent Documents

init	Cite.No.	Patent No.	Date	Patentee	Kind	Class	Subclass
Va	1	5943560	1999-08-24	Chang, et al.			
		5540785	1996-07-30	Dennard, et al.			
B		5462883	1995-10-31	Dennard, et al.			

## **Signature**

Examiner Name	Date			
1 Della	7/22/04			